



DXTP22040DFGQ

40V PNP LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

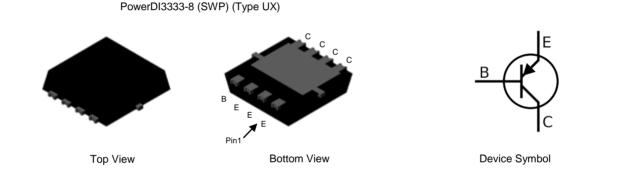
- BV_{CEO} > -40V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- I_C = -2A Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -320mV @ -1A
- Complementary NPN Type: DXTN22040DFGQ
- Rated to +175°C Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXTP22040DFGQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)

Applications

- High-Side Switch
- Supply Line Switching
- Motor Driving



Ordering Information (Note 4)

| Part Number | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|--|------------|---------|--------------------|-----------------|-------------------|
| DXTP22040DFGQ-7 | Automotive | 2K4 | 7 | 12 | 2,000 |
| Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. | | | | | |

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

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3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2K4 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



DXTP22040DFGQ

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|------------------------------|------------------|-------|------|--|
| Collector-Base Voltage | V _{CBO} | -50 | V | |
| Collector-Emitter Voltage | V _{CEO} | -40 | V | |
| Emitter-Base Voltage | V _{EBO} | -7 | V | |
| Continuous Collector Current | lc | -2 | A | |
| Peak Pulse Collector Current | I _{CM} | -3 | | |
| Continuous Base Current | IB | -100 | mA | |
| Peak Pulse Base Current | I _{BM} | -200 | | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|---|-----------------------------------|------------------|------|------|
| | (Note 5) | | 1.07 | |
| Power Dissipation | (Note 6) | PD | 2.3 | W |
| | (Note 7) | | 3.4 | W |
| | (Note 5) | | 140 | °C/W |
| Thermal Resistance, Junction to Ambient | (Note 6) | R _{0JA} | 65 | °C/W |
| | (Note 7) | | 44 | °C/W |
| Thermal Resistance, Junction to Leads (Note | R _{θJL} | 11 | °C/W | |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +175 | °C | |

ESD Ratings (Note 9)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|---|---------|-------|------|-------------|
| Electrostatic Discharge – Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge – Machine Model | ESD MM | 400 | V | С |
| Notes: 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state. | | | | |

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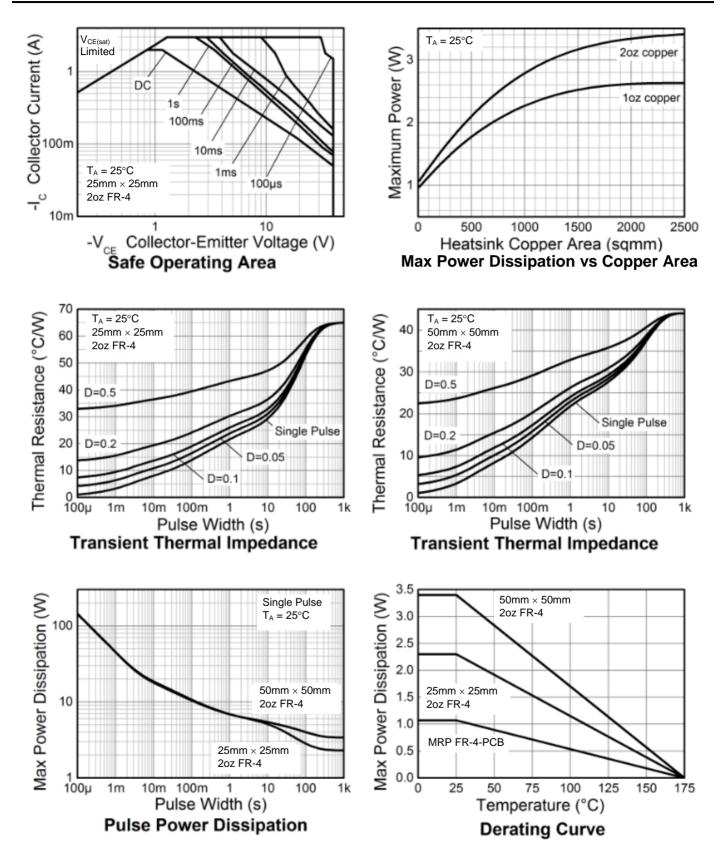
6. Same as Note 5, except the device is mounted on 25mm \times 25mm 2oz copper.

7. Same as Note 5, except the device is mounted on 50mm \times 50mm 2oz copper.

Thermal resistance from junction to solder-point (at the collector tab).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

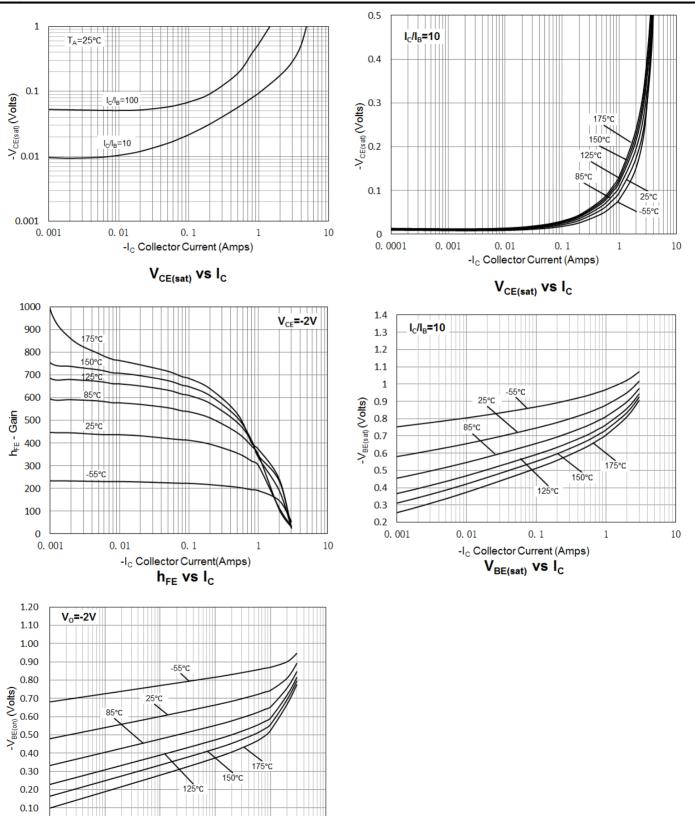
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|--|--------------------------|-----------------------------------|--------------------------------------|----------------------|--|
| Collector-Base Breakdown Voltage | BV _{CBO} | -50 | -71 | _ | V | I _C = -100μA |
| Collector-Emitter Breakdown Voltage (Note 10) | BVCEO | -40 | -58 | _ | V | I _C = -10mA |
| Emitter-Base Breakdown Voltage | BV _{EBO} | -7 | -8.5 | _ | V | I _E = -100μA |
| Collector-Base Cut-Off Current | I _{СВО} | _ | -1 -0.1 | -0.1 -20 | μA | V _{CB} = -50V V _{CB} = -50V, T _A = +150°C |
| Emitter-Base Cut-Off Current | I _{EBO} | _ | -1 | -20 | nA | V _{EB} = -6V |
| Collector-Emitter Cut-Off Current | ICES | _ | -1 | -20 | nA | $V_{CE} = -40V, V_{BE} = 0V$ |
| Static Forward Current Transfer Ratio (Note 10) | hFE | 340 300 200 120 | 410 354 303 203 | 900 — | _ | $I_{C} = -100 \text{mA}, V_{CE} = -2V$ $I_{C} = -500 \text{mA}, V_{CE} = -2V$ $I_{C} = -1A, V_{CE} = -2V$ $I_{C} = -2A, V_{CE} = -2V$ |
| Collector-Emitter Saturation Voltage (Note 10) | V _{CE(sat)} | _ | -56 -48 -81 -146 -218 | -140 -170 -320 -400 -600 | mV | I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -1A, I _B = -100mA I _C = -2A, I _B = -200mA I _C = -3A, I _B = -300mA |
| Collector-Emitter Saturation Resistance (Note 10) | R _{CE(sat)} | _ | — | 320 | mΩ | $I_{C} = -1A, I_{B} = -100mA$ |
| Base-Emitter Saturation Voltage (Note 10) | V _{BE(sat)} | _ | -0.88 | -1 | V | $I_{C} = -1A, I_{B} = -100mA$ |
| Base-Emitter Turn-On Voltage (Note 10) | V _{BE(on)} | | -0.76 | -0.9 | V | $I_{C} = -1A, V_{CE} = -2V$ |
| Transition Frequency | f⊤ | - | 120 | - | MHz | Ic = -50mA, V _{CE} = -10V f = 100MHz |
| Output Capacitance | C _{obo} | _ | 12 | _ | pF | V _{CB} = -10V, f = 1MHz |
| Switching Characteristics | t _{delay} t _{rise} t _{storage} t _{fall} | | 10 144 704 48.5 | | ns ns ns ns | V _{CC} = -10V, I _C = -500mA I _{B1} = -I _{B2} = -50mA |

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



DXTP22040DFGQ

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



0.001

001 0. 01 0. 1 -I_C Collector Current (Amps)

V_{BE(on)} vs I_C

0.00

0.0001

10

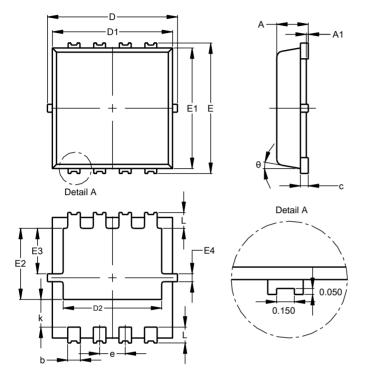
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

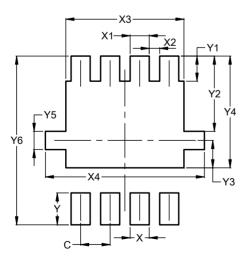


| PowerDI3333-8 (SWP) | | | | | | |
|------------------------------------|------|------|------|--|--|--|
| (Type UX) Dim Min Max Typ | | | | | | |
| A | 0.75 | 0.85 | Typ | | | |
| | | | 0.80 | | | |
| A1 | 0.00 | 0.05 | | | | |
| b | 0.25 | 0.40 | 0.32 | | | |
| С | 0.10 | 0.25 | 0.15 | | | |
| D | 3.20 | 3.40 | 3.30 | | | |
| D1 | 2.95 | 3.15 | 3.05 | | | |
| D2 | 2.30 | 2.70 | 2.50 | | | |
| E | 3.20 | 3.40 | 3.30 | | | |
| E1 | 2.95 | 3.15 | 3.05 | | | |
| E2 | 1.60 | 2.00 | 1.80 | | | |
| E3 | 0.95 | 1.35 | 1.15 | | | |
| E4 | 0.10 | 0.30 | 0.20 | | | |
| е | _ | _ | 0.65 | | | |
| k | 0.50 | 0.90 | 0.70 | | | |
| L | 0.30 | 0.50 | 0.40 | | | |
| θ | 0° | 12° | 10° | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 0.650 |
| Х | 0.420 |
| X1 | 0.420 |
| X2 | 0.230 |
| X3 | 2.600 |
| X4 | 3.500 |
| Y | 0.700 |
| Y1 | 0.550 |
| Y2 | 1.650 |
| Y3 | 0.600 |
| Y4 | 2.450 |
| Y5 | 0.400 |
| Y6 | 3.700 |



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